TOSHIBA HIGH EFFICIENCY DIODE STACK (HED) SILICON EPITAXIAL TYPE

10DL2C48A, 10FL2C48A, U10DL2C48A, U10FL2C48A

SWITCHING TYPE POWER SUPPLY APPLICATION.

CONVERTER & CHOPPER APPLICATION.

Repetitive Peak Reverse Voltage : V_{RRM}=200, 300V

• Average Output Rectified Current: IO=10A

• Ultra Fast Reverse-Recovery Time: trr=35ns Max.

• Low Switching Losses and Output Noise.

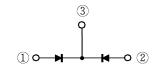
Unit in mm

10DL2C48A, 10FL2C48A	U10DL2C48A, U10FL2C48A			
10.3 MAX. 5.0 1.6 MAX. 1.6 MAX. 2.54 ± 0.25 2.54 ± 0.25 2.54 ± 0.25 2.54 ± 0.25 3. CATHOI	2.54±0.25			
JEDEC —	JEDEC —			
EIAJ —	EIAJ —			
TOSHIBA 12-10D1A	TOSHIBA 12-10D2A			

MAXIMUM RATINGS

CHARACTERISTIC		SYMBOL	RATING	UNIT	
	10DL2C48A		200	v	
Repetitive Peak Reverse Voltage	U10DL2C48A	$v_{ m RRM}$			
	10FL2C48A	V KKM	900		
	U10FL2C48A	1	300		
Average Output Rectified Current		IO	10	A	
Peak One Cycle Surge Forward		Trong	50 (50Hz)	Hz)	
Current		I _{FSM}	55 (60Hz)] A	
Junction Temperature		T_{j}	-40~150	°C	
Storage Temperature Range		$\mathrm{T_{stg}}$	-40~150	°C	

POLARITY



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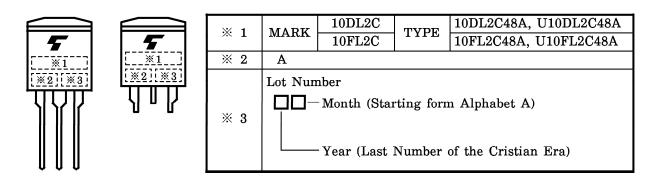
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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
10DL2C48A	77	T	_	-	0.98	V	
		$ m V_{FM}$	$I_{\text{FM}} = 5A$	_	_	1.3	v
Repetitive Peak Reverse Current		I_{RRM}	V _{RRM} =Rated	_		10	μ A
Reverse Recovery Time t ₁		t _{rr}	$I_F = 2A$, di/dt= $-20A/\mu s$	_	_	35	ns
Forward Recovery Time		tfr	$I_{\mathbf{F}} = 1A$	_	_	100	ns
Thermal Resistance		R _{th (j-c)}	DC Total, Junction to Case	_	_	2.5	°C/W

 $V_{\mbox{\scriptsize FM}},\,I_{\mbox{\scriptsize RRM}},\,t_{\mbox{\scriptsize rr}},\,t_{\mbox{\scriptsize fr}}:A$ Value of one cell.

MARKING



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